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# **Surface/Interface and Stress Effects in Electronic Material Nanostructures**

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## CONTENTS

Preface .....	xiii
Materials Research Society Symposium Proceedings .....	xiv

### PART I: TUTORIAL

Effects of Strain on the Electronic and Vibrational Properties of Semiconductors and Semiconductor Microstructures .....	3
<i>Fred H. Pollak</i>	

### PART II: NANOSTRUCTURE FORMATION: GROWTH AND STRESS EFFECTS

Desorption and Segregation of Indium and its Dependence on Surface As-Coverage .....	31
<i>M.J. Ekenstedt, H. Yamaguchi, and Y. Horikoshi</i>	

Thermal Stability of GaAs/InGaP and InGaP/(In)GaAs Interfaces .....	37
<i>F. Hyuga, T. Nittono, K. Watanabe, and T. Furuta</i>	

Uniaxial Stress Applied to p-type GaAs/AlGaAs Heterostructures: Influence on Heavy Hole Subbands .....	43
<i>Ole P. Hansen, Janus S. Olsen, W. Kraak, B. Saffian, N. Minina, and A. Savin</i>	

Reduction of Lateral Dimension on InGaAs/GaAs Multilayers on Non-(111)V-Grooved GaAs(100) Substrate by Chemical Beam Epitaxy .....	49
<i>Sung-Bock Kim, Jeong-Rae Ro, Seong-Ju Park, and El-Hang Lee</i>	

Facet Evolution and Selective Growth of GaAs/AlGaAs Lateral Structure Grown by Growth-Interrupted Chemical Beam Epitaxy Using Unprecacked Monoethylarsine .....	55
<i>Jeong-Rae Ro, Sung-Bock Kim, Seong-Ju Park, Jihwa Lee, and El-Hang Lee</i>	

High Quality AlGaAs Regrowth on Oxide-Free Al <sub>x</sub> Ga <sub>1-x</sub> As (x=0.26) by Metalorganic Chemical Vapor Deposition .....	61
<i>Kun-Jing Lee, Z.C. Huang, and J.C. Chen</i>	

RHEED Intensity Observation of AlAs and GaAs by <i>In Situ</i> Etching Using Arsenic Tribromide .....	67
<i>T. Kaneko, T. Säger, and K. Eberl</i>	

<b>*Kinetic Studies of Nanoscale Crystallization in Electronic Materials</b> .....	<b>73</b>
<i>C. Hayzelden and J.L. Batstone</i>	
<b>Growth and Characterization of Pseudomorphic <math>\text{Ge}_{1-y}\text{C}_y</math> and <math>\text{Si}_{1-y}\text{C}_y</math> Alloy Layers on Si Substrates</b> .....	<b>87</b>
<i>K. Brunner, K. Eberl, and W. Winter</i>	
<b>Ab-Initio Calculations of <math>\text{C}_x\text{Si}_{1-x-y}\text{Ge}_y</math> Compounds for Silicon-Based Heterojunction Devices</b> .....	<b>93</b>
<i>M.A. Berding, A. Sher, and M. Van Schilfgaarde</i>	

**PART III: FABRICATED NANOSTRUCTURES: STRESS EFFECTS**

<b>*Damage, Strain and Quantum Confinement Issues in Dry Etched Semiconductor Nanostructures</b> .....	<b>99</b>
<i>Y.S. Tang and C.M. Sotomayor Torres</i>	
<b>Strain Measurement in Two-Dimensional Nanoscale Si Gratings by High Resolution X-ray Diffraction</b> .....	<b>109</b>
<i>So Tanaka, Christopher C. Umbach, Qun Shen, and Jack M. Blakely</i>	
<b>Fabrication of Novel III-N and III-V Modulator Structures by ECR Plasma Etching</b> .....	<b>115</b>
<i>S.J. Pearton, C.R. Abernathy, J.D. MacKenzie, J.R. Mileham, R.J. Shul, S.P. Kilcoyne, M. Hagerott-Crawford, F. Ren, W.S. Hobson, and J.M. Zavada</i>	
<b>Stress Distributions in Free Standing Quantum Well Dots and Wires</b> .....	<b>121</b>
<i>N.A. Gippius, S.G. Tikhodeev, R. Steffen, T. Koch, and A. Forchel</i>	
<b>Stark Effects on Band Gap and Surface Phonons of Semiconductor Quantum Dots in Dielectric Hosts</b> .....	<b>127</b>
<i>R. Mu, A. Ueda, Y-S. Tung, D.O. Henderson, Jane G. Zhu, John D. Budai, and W.C. White</i>	
<b>Three-Dimensional Epitaxy: Thermodynamic Stability Range of Coherent Germanium Nanocrystallites in Silicon Host</b> .....	<b>133</b>
<i>S. Balasubramanian, G. Ceder, and K.D. Kolenbrander</i>	

**PART IV: POROUS SILICON: MATERIALS AND OPTICAL PROPERTIES**

<b>*Localization Phenomena, Photoluminescence, and Raman Scattering in nc-Si and nc-Si/<math>\alpha</math>-<math>\text{SiO}_2</math> Composites</b> .....	<b>141</b>
<i>S. Veprek, T. Wirschem, M. Rückschloß, C. Ossadnik, J. Dian, S. Perna, and I. Gregora</i>	

\*Invited Paper

<b>Oxygen Related Defect Center Red Room Temperature Photoluminescence in As Made and Oxidized Porous Silicon</b> .....	<b>153</b>
<i>S.M. Prokes and W.E. Carlos</i>	
<b>SiO<sub>x</sub> Related Photoluminescence Excitation in Porous Silicon</b> .....	<b>159</b>
<i>T.V. Torchinskaya, N.E. Korsunskaya, B.R. Dzumaev, and M.K. Sheinkman</i>	
<b>Photovoltaic and Electroluminescent Properties of Stain-Etched Porous Silicon Based Heterojunctions</b> .....	<b>167</b>
<i>D. Dimova-Malinovska, M. Tzolov, M. Kamenova, N. Tzenov, M. Sendova-Vassileva, and D. Nesheva</i>	
<b>Microstructural Investigation of Porous Silicon Depth Profile by Direct Surface Force Microscopy</b> .....	<b>173</b>
<i>D.C. Chang, V. Baranauskas, I. Doi, and T. Prohaska</i>	
<b>Femtosecond Nonlinear Transmission Study of Free-Standing Porous Silicon Films</b> .....	<b>179</b>
<i>V. Klimov, D. McBranch, and V. Karavanskii</i>	
<b>Effect of <math>\gamma</math>-Irradiation on Photoluminescence of Porous Silicon</b> .....	<b>185</b>
<i>E.V. Astrova, V.V. Emtsev, A.A. Lebedev, D.S. Poloskin, A.D. Remenyuk, Yu.V. Rud', and R.F. Vitman</i>	
<b>Formation of Intensive Photoluminescence in Porous Silicon</b> .....	<b>193</b>
<i>V.A. Makara, M.S. Boltovets, O.V. Vakulenko, O.I. Datsenko, and O.V. Rudenko</i>	
<b>Restoration of Porous Silicon Luminescence in Water Vapour</b> .....	<b>197</b>
<i>M.S. Brodin, V.N. Bykov, D.B. Dan'ko, R.D. Fedorovich, A.A. Kipen', O.E. Kiyayev, G.A. Naumovets, and N.I. Yanushevskii</i>	
<b>Linear Polarization of Porous Si Photoluminescence</b> .....	<b>203</b>
<i>N.A. Gippius, S.G. Tikhodeev, A.I.L. Efros, M. Rosen, D. Kovalev, M. Ben Chorin, J. Diener, and F. Koch</i>	
<b>Towards a Microscopic Interpretation of the Dielectric Function of Porous Silicon</b> .....	<b>209</b>
<i>U. Rossow, U. Frotscher, D.E. Aspnes, and W. Richter</i>	
<b>Photoluminescence Properties of Er-Doped Porous Silicon</b> .....	<b>215</b>
<i>U. Hömmerich, X. Wu, F. Namavar, A.M. Cremins-Costa, and K.L. Bray</i>	

**PART V: DEPOSITION AND SURFACE PROPERTIES  
OF SEMICONDUCTOR NANOSTRUCTURES**

<b>Phase Transformation of Germanium Ultrafine Particles at High Temperature</b> .....	223
<i>S. Nozaki, S. Sato, H. Ono, H. Morisaki, and M. Iwase</i>	
<b>Visible Luminescence from Surface-Oxidized Silicon Nanostructures: Three Region Model</b> .....	229
<i>Yoshihiko Kanemitsu</i>	
<b>Possibility of Self-Trapped Excitons in Silicon Nanocrystallites</b> .....	235
<i>G. Allan, C. Delerue, and M. Lannoo</i>	
<b>Substrate Surface Dependence of the Microstructure of <math>\mu\text{c-Si,Ge:H}</math> Deposited by Reactive Magnetron Sputtering (RMS)</b> .....	241
<i>S.M. Cho, K. Christensen, D. Wolfe, H. Ying, D.R. Lee, G. Lucovsky, and D.M. Maher</i>	
<b>On the Origin of Visible Luminescence from <math>\text{SiO}_2</math> Films Containing Ge Nanocrystals</b> .....	247
<i>K.S. Min, K.V. Shcheglov, C.M. Yang, R.P. Camata, Harry A. Atwater, M.L. Brongersma, and A. Polman</i>	
<b>Electrical Characteristics and Temperature Effects of Electroluminescing Silicon Nanocrystals</b> .....	253
<i>E.W. Forsythe, E.A. Whittaker, D. Morton, B.A. Khan, B.S. Sywe, Y. Lu, S. Liang, C. Gorla, and G.S. Tompa</i>	
<b>Synthesis of Size-Classified Silicon Nanocrystals</b> .....	259
<i>Renato P. Camata, Harry A. Atwater, Kerry J. Vahala, and Richard C. Flagan</i>	
<b>Room Temperature Emission from Erbium Nanoparticles Embedded in a Silicon Matrix</b> .....	265
<i>A. Thilderkvist, J. Michel, S.-T. Ngiam, L.C. Kimerling, and K.D. Kolenbrander</i>	
<b>Carrier Transport in Silicon Nanocrystallite-Based Multilayer Electroluminescent Devices</b> .....	271
<i>T.A. Burr and K.D. Kolenbrander</i>	
<b>Control of Silicon Nanocrystallite Luminescence Behavior through Surface Treatments</b> .....	277
<i>A.A. Seraphin, S.-T. Ngiam, and K.D. Kolenbrander</i>	
<b>Investigation of Local Structures around Luminescent Centers in Doped Nanocrystal Phosphors</b> .....	283
<i>Y.L. Soo, S.W. Huang, Z.H. Ming, Y.H. Kao, E. Goldburt, R. Hodel, B. Kulkarni, and R. Bhargava</i>	

<b>Nonlinear Optical Properties of CuS Nanocrystals with Modified Surface</b> .....	<b>289</b>
<i>K.V. Yumashev, V.P. Mikhailov, A.M. Malyarevich, P.V. Prokoshin, V.S. Gurin, and M.V. Artemyev</i>	

<b>ZnS/Si/ZnS Quantum Well Structures for Visible Light Emission</b> .....	<b>295</b>
<i>Eric Bretschneider, Albert Davydov, Clint McCreary, Li Wang, Timothy J. Anderson, H. Paul Maruska, Peter E. Norris, Ian Goepfert, and Theodore D. Moustakas</i>	

<b>Persistent Spectral Hole-Burning of CuCl Semiconductor Quantum Dots</b> .....	<b>301</b>
<i>Shinji Okamoto and Yasuaki Masumoto</i>	

**PART VI: SEMICONDUCTOR INTERFACES**

<b>*Continuum Elastic Strain Effects at Semiconductor Interfaces</b> .....	<b>309</b>
<i>T.P. Pearsall</i>	

<b>Incorporation of Nitrogen Atoms at Si/SiO<sub>2</sub> Interfaces of Field Effect Transistors (FETs) to Improve Device Reliability</b> .....	<b>321</b>
<i>G. Lucovsky, D.R. Lee, Z. Jing, J.L. Whitten, C. Parker, and J.R. Hauser</i>	

<b>Theoretical Modelling of the Surface Oxidation of a Silicon Carbide Nanopowder, Based on the <math>\nu(\text{SiH})</math> Frequency Evolution</b> .....	<b>327</b>
<i>Marie-Isabelle Baraton and Sylvette Besnainou</i>	

<b>Characterization of MOS Structures with Ultra-Thin Tunneling Oxynitride</b> .....	<b>333</b>
<i>H. Fujioka, C. Wann, D. Park, and C. Hu</i>	

<b>Interfacial Defect Control for Infrared Conversion Widening of Silicon Single-Crystal Solar Cells</b> .....	<b>339</b>
<i>Z.T. Kuznicki</i>	

<b>Stress Effects in 2D Arsenic Diffusion in Silicon</b> .....	<b>345</b>
<i>V. Rao and W. Zagodzón-Wosik</i>	

<b>Surface Effects in Silicon Doping with Boron during Proximity Rapid Thermal Diffusion</b> .....	<b>351</b>
<i>S. Mone, W. Zagodzón-Wosik, and M. Rastogi</i>	

\*Invited Paper

**PART VII: MATERIALS CHARACTERIZATION I: X-RAY  
AND STRAIN MEASUREMENTS**

<b>*Structural Characterization of Reactive Ion Etched Semiconductor Nanostructures Using X-ray Reciprocal Space Mapping</b> .....	<b>359</b>
<i>G. Bauer, A.A. Darhuber, and V. Holy</i>	
<b>*Study of Periodic Surface Nanostructures Using Coherent Grating X-ray Diffraction (CGXD)</b> .....	<b>371</b>
<i>Qun Shen</i>	
<b>Real Time Measurement of Epilayer Strain Using a Simplified Wafer Curvature Technique</b> .....	<b>381</b>
<i>J.A. Floro, E. Chason, and S.R. Lee</i>	
<b>Optical and Structural Characterization of Arsenide/Phosphide Interfaces Formed by Flow Modulation Epitaxy</b> .....	<b>387</b>
<i>D.T. Emerson, J.A. Smart, K.L. Whittingham, E.M. Chumbes, and J.R. Shealy</i>	
<b>Determining Thin Film Density by Energy-Dispersive X-ray Reflectivity: Application to a Spin-on-Glass Dielectric</b> .....	<b>393</b>
<i>W.E. Wallace and W.L. Wu</i>	
<b>Combine Spectroscopic Ellipsometry and Grazing X-ray Reflectance for Fine Characterization of Complex Epitaxial Structures</b> .....	<b>399</b>
<i>P. Boher and J.L. Stehle</i>	
<b>A New Technique for Depth Profiling on a Nanometer Scale</b> .....	<b>407</b>
<i>H. Schwenke, J. Knoth, R. Günther, G. Wiener, and R. Bormann</i>	

**PART VIII: MATERIALS CHARACTERIZATION II: SURFACE PASSIVATION AND  
STRUCTURAL DEFECT STUDIES**

<b>The Uniformity of Surface Passivation After (NH<sub>4</sub>)<sub>2</sub>S Treatment Studied by Near-Field Scanning Optical Microscopy</b> .....	<b>415</b>
<i>Jutong Liu and T.F. Kuech</i>	
<b>A New Method for the Electronic and Chemical Passivation of GaAs Surfaces Using CS<sub>2</sub></b> .....	<b>421</b>
<i>Ju-Hyung Lee, Yanzhen Xu, Veronica A. Burrows, and Paul F. McMillan</i>	

\*Invited Paper

<b>Cathodoluminescence Study of Diffusion Length and Surface Recombination Velocity in III-V Multiple Quantum Well Structures</b> .....	<b>429</b>
<i>L.-L. Chao, M.B. Freiler, M. Levy, J.-L. Lin, G.S. Cargill, III, R.M. Osgood, Jr., and G.F. McLane</i>	

<b>*Transmission Electron Diffraction Techniques for NM Scale Strain Measurement in Semiconductors</b> .....	<b>435</b>
<i>J. Vanhellemont, K.G.F. Janssens, S. Frabboni, P. Smeys, R. Balboni, and A. Armigliato</i>	

<b>Analysis of Localized Small Defect in ULSs</b> .....	<b>447</b>
<i>K. Fukumoto, H. Maeda, Y. Mashiko, M. Sekine, and H. Koyama</i>	

<b>Ge-Related Interfacial Defects in SiGe Alloy Structures</b> .....	<b>453</b>
<i>Patricia J. Macfarlane, M.E. Zvanut, W.E. Carlos, M.E. Twigg, and P.E. Thompson</i>	

<b>Dislocation Formation in Trench-Based Dynamic Random Access Memory (DRAM) Chips</b> .....	<b>459</b>
<i>H. Ho, E. Hammerl, R. Stengl, and J. Benedict</i>	

<b>Determination of Bulk Mismatch Values in Heterostructures by TEM/CBED</b> .....	<b>467</b>
<i>A. Armigliato, R. Balboni, and S. Frabboni</i>	

**PART IX: METAL, CERAMIC AND POLYMER NANOSTRUCTURES**

<b>*Stress Evolution in Ultra Thin Sputtered Films</b> .....	<b>475</b>
<i>Quanmin Su, R.C. Cammarata, and Manfred Wuttig</i>	

<b>*Use of Advantageous Impurity Effects in Metallization</b> .....	<b>485</b>
<i>S.P. Murarka</i>	

<b>Interface Stresses in Nanostructured Multilayered Materials</b> .....	<b>497</b>
<i>R.C. Cammarata and K. Sieradzki</i>	

<b>Measurement of Young's Modulus and Poisson's Ratio of Free-Standing Ag/Cu Multilayered Thin Films</b> .....	<b>501</b>
<i>Haibo Huang and Frans Spaepen</i>	

<b>Nanocrystallization Studies in Co and Fe-Rich Amorphous Alloys</b> .....	<b>507</b>
<i>S. Aburto, M. Jiménez, R. Gómez, V. Marquina, M.L. Marquina, R. Ridaura, P. Santiago, L. Rendon, and R. Valenzuela</i>	

<b>Characterization of the Interface between Metal Contacts and Epilayers of Doped Silicon Carbide</b> .....	<b>513</b>
<i>M.A. George, D.J. Larkin, J. Petit, A. Burger, S.H. Morgan, and W.E. Collins</i>	

\*Invited Paper



<b>Magnetic Properties of Nanoscale Iron Particles Photodeposited in Glass</b> .....	<b>519</b>
<i>D. Sunil, H.D. Gafney, C. Tsang, M.H. Rafailovich, J. Sokolov, R.J. Gambino, and D.M. Huang</i>	
<b>Crystalline Structure and Morphology of the Phases in MgO, TiO<sub>2</sub> and ZrO<sub>2</sub> Prepared by the Sol-gel Technique</b> .....	<b>523</b>
<i>Bokhimi, J.L. Boldu, E. Muñoz, O. Novaro, T. Lopez, and R. Gomez</i>	
<b>Gold Nanocomposites Prepared by Reactive Sputtering</b> .....	<b>529</b>
<i>L. Maya, M. Paranthaman, T. Thundat, W.R. Allen, A.L. Glover, and J.C. Mabon</i>	
<b>Thermal and Mechanical Characteristics of Polyimide Based Ceramers</b> .....	<b>535</b>
<i>P.R. McDaniel and T.L. StClair</i>	
<b>Author Index</b> .....	<b>541</b>
<b>Subject Index</b> .....	<b>545</b>